SGS-THOMSON MICROELECTRONICS

BUT70

HIGH POWER NPN SILICON TRANSISTOR

- SGS-THOMSON PREFERRED SALESTYPE
- NPN TRANSISTOR
- HIGH CURRENT CAPABILITY
- FAST SWITCHING SPEED
- VERY LOW SATURATION VOLTAGE AND HIGH GAIN

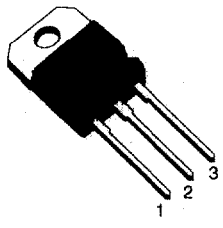
APPLICATION

- SWITCHING REGULATORS
- MOTOR CONTROL
- HIGH FREQUENCY AND EFFICENCY CONVERTERS

DESCRIPTION

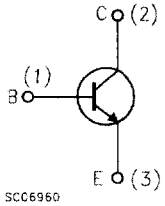
The BUT70 is a Multiepitaxial planar NPN transistor in TO-218 plastic package.

It's intented for use in high frequency and efficiency converters such us motor controllers and industrial equipment.



TO-218

INTERNAL SCHEMATIC DIAGRAM



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V_{CEV}	Collector-emitter Voltage (V_{BE} = -1.5V)	200	V
V_{CEO}	Collector-emitter Voltage (I_B = 0)	125	V
V_{EBO}	Emitter-Base Voltage (I_C = 0)	7	V
$I_{E(RMS)}$	Emitter Current	40	A
I_{EM}	Emitter Peak Current	120	A
I_B	Base Current	8	A
I_{BM}	Base Peak Current	24	A
P_{tot}	Total Power Dissipation at T_{case} < 25 °C	200	W
T_{stg}	Storage Temperature	-65 to 150	°C
T_j	Max Operating Junction Temperature	150	°C

THERMAL DATA

$R_{thj\text{-}case}$	Thermal Resistance Junction-case	Max	0.63	°C/W

ELECTRICAL CHARACTERISTICS (T_{case} = 25 °C unless otherwise specified)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I_{CER}	Collector Cut-off Current (R_{BE} = 5Ω)	V_{CE} = V_{CEV} V_{CE} = V_{CEV} T_c = 100°C			1 5	mA mA
I_{CEV}	Collector Cut-off Current	V_{CE} = V_{CEV} V_{BE} = -1.5V V_{CE} = V_{CEV} V_{BE} = - 1.5V T_C =100°C			1 4	mA mA
I_{EBO}	Emitter Cut-off Current (I_C = 0)	V_{EB} = - 5 V			1	mA
$V_{CEO(sus)}$*	Collector-Emitter Sustaining Voltage	I_C = 0.2A L = 25 mH	125			V
V_{EBO}	Emitter-base Voltage (I_C = 0)	I_E = 50 mA	7			V
$V_{CE(sat)}$*	Collector-Emitter Saturation Voltage	I_C = 70 A I_B = 7 A I_C = 70 A I_B = 7 A T_j = 100°C I_C = 35 A I_B = 1.75 A I_C = 35 A I_B = 1.75 A T_j = 100°C			0.9 1.5 0.9 1.2	V V V V
$V_{BE(sat)}$*	Base-Emitter Saturation Voltage	I_C = 70 A I_B = 7 A I_C = 70 A I_B = 7 A T_j = 100°C I_C = 35 A I_B = 1.75 A I_C = 35 A I_B = 1.75 A T_j = 100°C			1.8 1.9 1.4 1.4	V V V V
di_c/d_t*	Rated of Rise of on-state Collector Current	V_{CC} = 100 V R_C = 0 I_{B1} = 3.5 A t_p =3 µS T_j = 100°C	140			A/µs

* Pulsed: Pulse duration = 300 µs, duty cycle < 2 %

INDUCTIVE LOAD

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
t_r	Rise Time	V_{CC} = 90 V I_C = 35 A			1.8	µs
t_s	Storage Time	V_{BB} = -5 V I_{B1} = 1.75 A			0.2	µs
t_f	Fall Time	R_{B2} = 1.4 Ω			0.35	µs
		L_C =0.13 mH T_J =100°C				
		V_{CLAMP} =125V				